CLAIMS

1. (Original) A conductive line for a semiconductor device including:

a first conductive layer;

a Titanium layer; and

a first Titanium rich Titanium Nitride layer between the first conductive layer and the Titanium layer.

2. (Original) A conductive line according to claim 1, wherein the first conductive layer is in direct contact with the first Titanium rich Titanium Nitride layer.

3. (Currently Amended) A conductive line according to claim 1 ~~or 2~~, wherein the Titanium layer is in direct contact with the first Titanium rich Titanium Nitride layer.

4. (Currently Amended) A conductive line according to ~~any one of the preceding claims~~ claim 1, wherein the first conductive layer is a metal layer.

5. (Original) A conductive line according to claim 4, wherein the first conductive layer is an aluminium alloy.

6. (Original) A conductive line according to claim 5, wherein the aluminium alloy is an aluminium copper alloy.

7. (Currently Amended) A conductive line according to ~~any one of the preceding claims~~ claim 1, wherein the Titanium layer is less than about 500 x 10^{-10}m (500 Angstroms) thick.

8. (Original) A conductive line according to claim 7, wherein the Titanium layer is from about 60 - 110 x 10^{-10}m (60 - 110 Angstroms) thick.

9. (Currently Amended) A conductive line according to ~~any one of the preceding claims~~ claim 1, wherein the first Titanium rich Titanium Nitride layer is a 250 - 500 x 10^{-10}m (250 - 500 Angstroms) layer.

10. (Currently Amended) A conductive line according to ~~any one of the preceding claims~~ claim 1, wherein the first conductive layer is a 4000 - 8000 x 10-10m (4000 - 8000 Angstroms) layer.

11. (Currently Amended) A conductive line according to ~~any one of the preceding claims~~ claim 1, further comprising a second Titanium rich Titanium Nitride layer, and wherein the first conductive layer is between the first and second Titanium rich Titanium Nitride layers.

12. (Original) A process for manufacturing a conductive line, comprising the steps of:

depositing a Titanium layer onto a substrate;

depositing a first Titanium rich Titanium Nitride layer to the other side of said Titanium layer relative to said substrate; and

depositing a first conductive layer to the other side of said first Titanium rich Titanium Nitride layer relative to said Titanium layer.

13. (Original) A process according to claim 12, wherein the Titanium layer is deposited directly onto said substrate.

14. (Currently Amended) A process according to claim 13 ~~or 14~~, wherein the first Titanium rich Titanium Nitride layer is deposited directly onto said Titanium layer.

15. (Currently Amended) A process according to claim 13, ~~14 or 15,~~ wherein the first conductive layer is deposited directly onto said first Titanium rich Titanium Nitride layer.

16. (Currently Amended) A process according to ~~any one of~~ claims 12 ~~to 15~~, further comprising the step of depositing a second Titanium rich Titanium Nitride layer to the other side of said first conductive layer relative to said first Titanium rich Titanium Nitride layer.

17. (Currently Amended) A process according to ~~any one of~~ claims 12 ~~to 16~~, wherein the first conductive layer is a metal layer.

18. (Original) A process according to claim 17, wherein the first conductive layer is an aluminium alloy.

19. (Original) A process according to claim 18, wherein the aluminium alloy is an aluminium copper alloy.

20. (Currently Amended) A process according to ~~any one of~~ claims 12 ~~to 19~~, wherein the Titanium layer is less than about 500 x 10-10m (500 Angstroms) thick.

21. (Original) A process according to claim 20, wherein the Titanium layer is from about 60 - 110 x 10-10m (60 - 110 Angstroms) thick.

22. (Currently Amended) A process according to ~~any one of~~ claims 12 ~~to 21~~, wherein the first Titanium rich Titanium Nitride layer is a 250 - 500 x 10-10m (250 - 500 Angstroms) layer.

23. (Currently Amended) A process according to ~~any one of~~ claims 12 ~~to 22~~, wherein the first conductive layer is a 4000 - 8000 x 10-10m (4000 - 8000 Angstroms) layer.

24. (Currently Amended) A silicon substrate having a plurality of conductive lines according to ~~any one of~~ claims 1 ~~to 11~~ thereon.

25. (Currently Amended) A semiconductor device including one or more conductive lines according to ~~any one of~~ claims 1 ~~to 11~~.

26. (Currently Amended) A memory including one or more conductive lines according to ~~any one of~~ claims 1 ~~to 11~~.

27. (Currently Amended) An integrated circuit including one or more conductive lines according to ~~any one of~~ claims 1 ~~to 11~~.